

ABSTRACT OF THE INVENTION

The present invention is directed to a process for preparing single crystal silicon, in ingot or wafer form, wherein crucible rotation is utilized to control the average axial temperature gradient in the crystal,  $G_0$ , as a function of radius (i.e.,  $G_0(r)$ ), particularly at or near the central axis. Additionally, crucible rotation  
5 modulation is utilized to obtain an axially uniform oxygen content therein.